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Product Data Sheet

UV LED Chip

EOLC-355-34

Rev. 03, 2017

Radiation	Type	Electrodes
Ultraviolet	AlGaN / sapphire	P + N up

<p style="text-align: right;">Unit : μm</p>	<p>Description</p> <ul style="list-style-type: none"> - Substrate: sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy - Emission area: 200 μm x 200 μm - Bottom area: 280 μm x 280 μm \pm 40 μm - Chip thickness: 75 \pm 10 μm - Bonding pad electrodes: (each) 90 μm - Electrodes spacing: 130 μm
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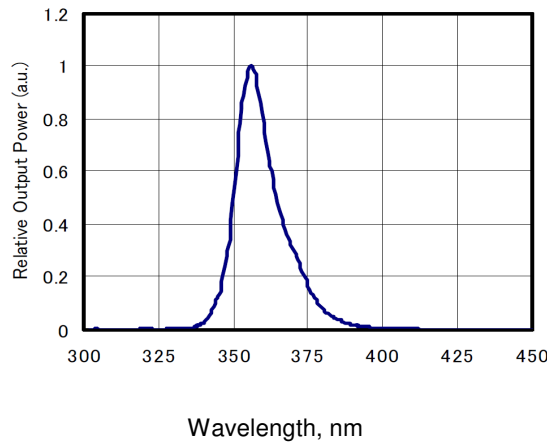
Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F	3.2	3.6	4.2	V
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μA
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	353		360	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		15		nm
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	0.5		1.5	mW

*Measured on bare chip on TO-18 header

Spectrum



Art. No. 111 001



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.